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Notice of Allowability	Application No.	Applicant(s)	
	10/001,557	LOJEK ET AL.	
	Examiner	Art Unit	
	Ida M Soward	2822	
The MAILING DATE of this communication ap All claims being allowable, PROSECUTION ON THE MERITS I herewith (or previously mailed), a Notice of Allowance (PTOL-8. NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.3	S (OR REMAINS) CLOSED in 5) or other appropriate commu RIGHTS. This application is s	nthis application. If not inclu unication will be mailed in du	ded e course. THIS
1. X This communication is responsive to the Applicants' ame	endment filed December 29, 20	<u>003</u> .	
2. ☑ The allowed claim(s) is/are <u>3-7 and 9</u> .			
3. \boxtimes The drawings filed on <u>10-24-01</u> are accepted by the Example 1.	miner.		
4. Acknowledgment is made of a claim for foreign priority a) All b) Some* c) None of the: 1. Certified copies of the priority documents hat 2. Certified copies of the priority documents hat 3. Copies of the certified copies of the priority of International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE noted below. Failure to timely comply will result in ABANDON THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be sub INFORMAL PATENT APPLICATION (PTO-152) which give the complete of Draftspee sub including changes required by the Notice of Draftspee 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examine Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in the department of	ve been received. ve been received in Application documents have been received. To of this communication to file IMENT of this application. mitted. Note the attached EXA ives reason(s) why the oath or just be submitted. erson's Patent Drawing Reviewer's Amendment / Comment or 1.84(c)) should be written on the the header according to 37 CF posit of BIOLOGICAL MATE	n No If in this national stage application is a reply complying with the result of the control of the declaration is deficient. If (PTO-948) attached in the Office action of the drawings in the front (not the control of t	equirements NOTICE OF
 Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SE Paper No./Mail Date) 6. ☐ Interview St Paper No./ 7. ☑ Examiner's 8. ☐ Examiner's 9. ☐ Other	formal Patent Application (Pummary (PTO-413), Mail Date Amendment/Comment Statement of Reasons for A ANIR ZARABIAN SORY PATENT EXAMINES	,

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DETAILED ACTION

This Office Action is in response to the Applicants' amendment filed December 29, 2003.

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Thomas Schneck on April 28, 2004.

The application has been amended as follows: "comprising" has been change to including in line 4 of the abstract.

Claim 1. Cancelled

Claim 2. Cancelled

Claim 3. The non-volatile memory cell of claim 4 <u>9</u> wherein said small spacer resides connection conductive layer extends along a <u>said opposite</u> side <u>of said small sidewall spacer</u> and on top of said main floating gate region.

Claim 4. The non-volatile memory cell of claim 3 9 wherein said first insulating portion is over the drain.

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Claim 6. The non-volatile memory cell of claim 4 <u>9</u> wherein said small sidewall spacer resides connection conductive layer extends along a side and on top of said main floating gate region, said thin tunnel oxide having a portion covering the main floating gate region except for an opening therein, with the connecting conductive layer making contact with the main floating gate region through said opening.

Claim 7. The non-volatile memory cell of claim 4 <u>4</u> wherein said first insulating portion is over said drain extends across the memory cell.

Claim 8. Cancelled

Claim 9. (Newly Added) A non-volatile memory cell comprising:

a semiconductor substrate, with a drain and a source in said substrate;

a conductive floating gate formed on said substrate between said source and drain with a first insulating layer separating said floating gate from said substrate, said floating gate including a main floating gate region and a small sidewall spacer, said first insulating layer including a first insulating portion separating said small sidewall spacer from said substrate and from said main floating gate region, a second insulating portion separating said main floating gate region from said substrate, wherein said first insulating portion is a thin tunnel oxide that is thinner than said second insulating portion, said small sidewall spacer having a first vertical side contacting said thin tunnel oxide and an opposite side that is electrically coupled to said main floating gate region by a conductive connecting layer extending over said opposite side of said sidewall spacer and extending past said thin tunnel oxide to contact said main floating gate region:

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a control gate formed over said floating gate; and a second insulating layer separating said control gate and said floating gate.

Allowable Subject Matter

Claims 3-9 are allowed.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

The following patents are cited to further show the state of the art with respect to non-volatile memory cell structures:

Hsieh et al. (US 6,229,176 B1)

Lee (6,159,797)

Lim et al. (6,124,170)

Mehta et al. (6,060,766).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ida M Soward whose telephone number is 571-272-1845. The examiner can normally be reached on Monday - Thursday, 6:30 am to 5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 571-272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

IMS April 28, 2004

AMIR ZARABIAN
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800